
2SJ181(L), 2SJ181(S)

Silicon P-Channel MOS FET

HITACHI

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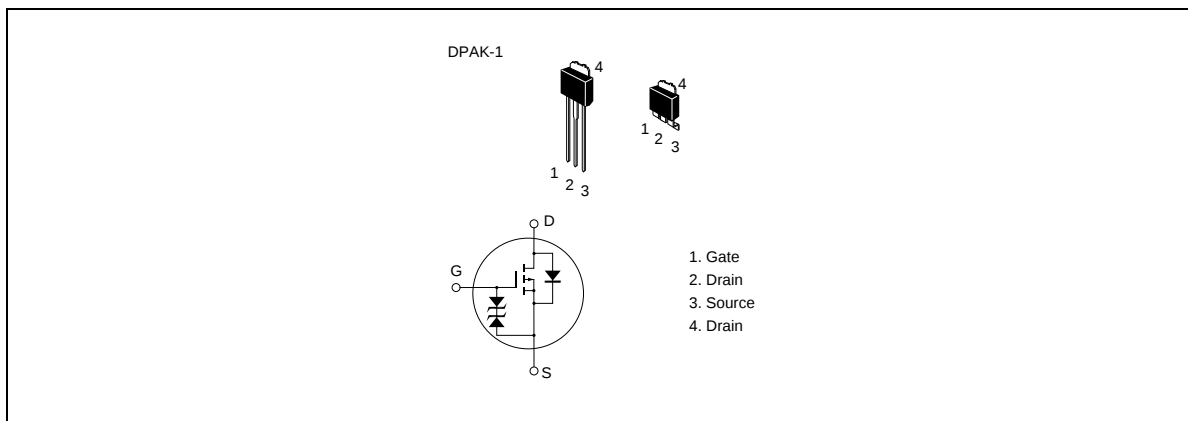
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline



2SJ181(L), 2SJ181(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	-600	V
Gate to source voltage	V_{GS}	±15	V
Drain current	I_D	-0.5	A
Drain peak current	$I_{D(pulse)}^{*1}$	-1.0	A
Body to drain diode reverse drain current	I_{DR}	-0.5	A
Channel dissipation	P_{ch}^{*2}	20	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

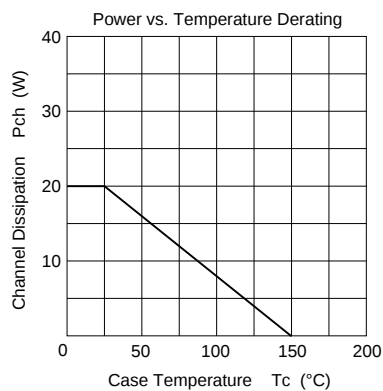
Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-600	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±15	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 12 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-100	μA	$V_{DS} = -500 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-2.0	—	-4.0	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	15	25	Ω	$I_D = -0.3 \text{ A}$, $V_{GS} = -10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	0.3	0.45	—	S	$I_D = -0.3 \text{ A}$, $V_{DS} = -20 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	220	—	pF	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	55	—	pF	
Reverse transfer capacitance	C_{rss}	—	13	—	pF	
Turn-on delay time	$t_{d(on)}$	—	7	—	ns	$I_D = -0.3 \text{ A}$, $V_{GS} = -10 \text{ V}$, $R_L = 100 \Omega$
Rise time	t_r	—	20	—	ns	
Turn-off delay time	$t_{d(off)}$	—	35	—	ns	
Fall time	t_f	—	35	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-0.85	—	V	$I_F = -0.5 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	230	—	ns	$I_F = -0.5 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 50 \text{ A}/\mu s$

Note 1. Pulse test

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